

LIGHT-EMITTERS WITH GROUP III-NITRIDE-BASED QUANTUM WELL ACTIVE REGIONS HAVING GAN INTERLAYERS

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Inventors: Chirag Gupta, Guangying Wang, Shubhra Pasayat

The Invention

UW-Madison researchers have developed a group III-nitride-based light emitting devices for efficient LED and laser applications. These devices have one or more quantum wells in the active region with a double well design using an AlInGaN alloy or an InGanN alloy adjacent to GaN interlayer, both of which are disposed between two barrier layers of an AlGaN alloy or low-In-content AlInGaN alloy.

Tech Fields

<u>Semiconductors & Integrated Circuits : Components & materials</u>

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